



# RF Power Field Effect Transistors

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed for GSM and GSM EDGE base station applications with frequencies from 1800 to 2000 MHz. Can be used in Class AB and Class C for all typical cellular base station modulations.

### GSM Application

- Typical GSM Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 1100$  mA,  $P_{out} = 125$  Watts CW,  $f = 1930$  MHz.  
 Power Gain — 16.5 dB  
 Drain Efficiency — 55%

### GSM EDGE Application

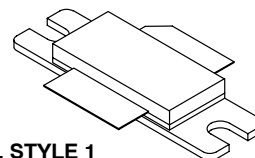
- Typical GSM EDGE Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 1100$  mA,  $P_{out} = 57$  Watts Avg., Full Frequency Band (1930-1990 MHz).  
 Power Gain — 17 dB  
 Drain Efficiency — 39%  
 Spectral Regrowth @ 400 kHz Offset = -60 dBc  
 Spectral Regrowth @ 600 kHz Offset = -74 dBc  
 EVM — 2.6% rms
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 1960 MHz, 125 Watts CW Output Power
- Typical  $P_{out}$  @ 1 dB Compression Point  $\approx 140$  Watts CW

### Features

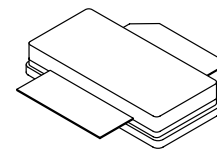
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

**MRF7S18125BHR3**  
**MRF7S18125BHSR3**

**1930-1990 MHz, 125 W CW, 28 V**  
**GSM, GSM EDGE**  
**LATERAL N-CHANNEL**  
**RF POWER MOSFETs**



**CASE 465-06, STYLE 1**  
**NI-780**  
**MRF7S18125BHR3**



**CASE 465A-06, STYLE 1**  
**NI-780S**  
**MRF7S18125BHSR3**

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +65	Vdc
Gate-Source Voltage	$V_{GS}$	-6.0, +10	Vdc
Operating Voltage	$V_{DD}$	32, +0	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_C$	150	°C
Operating Junction Temperature (1,2)	$T_J$	225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 81°C, 125 W CW		0.31	
Case Temperature 81°C, 71 W CW		0.35	

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{A}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{A}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 316\ \mu\text{A}$ )	$V_{GS(th)}$	1.2	1.9	2.7	Vdc
Gate Quiescent Voltage ( $V_{DS} = 28\text{ Vdc}$ , $I_D = 1100\text{ mA}$ )	$V_{GS(Q)}$	—	2.7	—	Vdc
Fixture Gate Quiescent Voltage (1) ( $V_{DD} = 28\text{ Vdc}$ , $I_D = 1100\text{ mA}$ , Measured in Functional Test)	$V_{GG(Q)}$	4	5.3	7	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 3.16\text{ A}$ )	$V_{DS(on)}$	0.1	0.2	0.3	Vdc

**Dynamic Characteristics (1)**

Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	1.15	—	pF
Output Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{oss}$	—	673	—	pF
Input Capacitance ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz)	$C_{iss}$	—	309	—	pF

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1100\text{ mA}$ ,  $P_{out} = 125\text{ W CW}$ ,  $f = 1930\text{ MHz}$ 

Power Gain	$G_{ps}$	15	16.5	18	dB
Drain Efficiency	$\eta_D$	51	55	—	%
Input Return Loss	IRL	—	-12	-7	dB

- $V_{GG} = 2 \times V_{GS(Q)}$ . Parameter measured on Freescale Test Fixture, due to resistive divider network on the board. Refer to Test Circuit schematic.
- Part internally matched both on input and output.

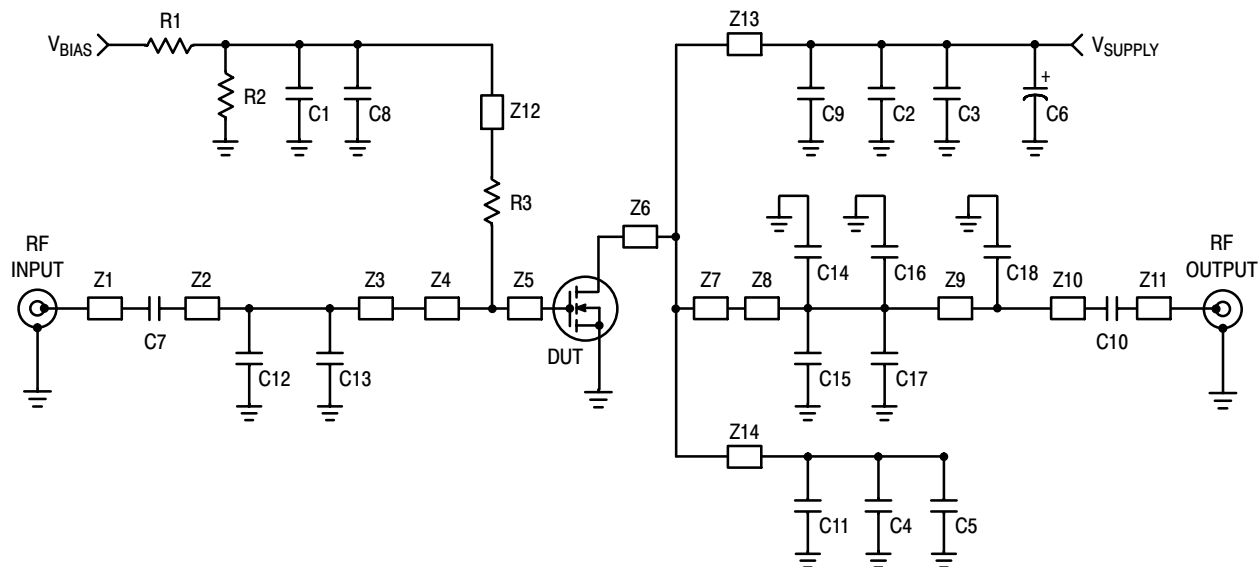
(continued)

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Typical Performances</b> (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$ , $I_{DQ} = 1100\text{ mA}$ , 1930-1990 MHz Bandwidth					
$P_{out}$ @ 1 dB Compression Point	$P_{1dB}$	—	140	—	W
IMD Symmetry @ 125 W PEP, $P_{out}$ where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands $> 2\text{ dB}$ )	$IMD_{sym}$	—	10	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	$VBW_{res}$	—	35	—	MHz
Gain Flatness in 60 MHz Bandwidth @ $P_{out} = 125\text{ W CW}$	$G_F$	—	1.02	—	dB
Average Deviation from Linear Phase in 60 MHz Bandwidth @ $P_{out} = 125\text{ W CW}$	$\Phi$	—	3.3	—	$^\circ$
Average Group Delay @ $P_{out} = 125\text{ W CW}$ , $f = 1960\text{ MHz}$	Delay	—	2.49	—	ns
Part-to-Part Insertion Phase Variation @ $P_{out} = 125\text{ W CW}$ , $f = 1960\text{ MHz}$ , Six Sigma Window	$\Delta\Phi$	—	6.7	—	$^\circ$
Gain Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )	$\Delta G$	—	0.016	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )	$\Delta P_{1dB}$	—	0.01	—	dBm/ $^\circ\text{C}$

**Typical GSM EDGE Performances** (In Freescale GSM EDGE Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1100\text{ mA}$ ,  $P_{out} = 57\text{ W}$  Avg., 1930-1990 MHz EDGE Modulation

Power Gain	$G_{ps}$	—	17	—	dB
Drain Efficiency	$\eta_D$	—	39	—	%
Error Vector Magnitude	EVM	—	2.6	—	% rms
Spectral Regrowth at 400 kHz Offset	SR1	—	-60	—	dBc
Spectral Regrowth at 600 kHz Offset	SR2	—	-74	—	dBc



Z1	0.227" x 0.083" Microstrip	Z8	0.200" x 0.083" Microstrip
Z2	0.697" x 0.083" Microstrip	Z9	1.045" x 0.083" Microstrip
Z3	0.618" x 0.083" Microstrip	Z10	0.071" x 0.083" Microstrip
Z4	0.568" x 1.000" Microstrip	Z11	0.227" x 0.083" Microstrip
Z5	0.092" x 1.000" Microstrip	Z12	1.280" x 0.080" Microstrip
Z6	0.095" x 1.000" Microstrip	Z13, Z14	0.760" x 0.080" Microstrip
Z7	0.565" x 1.000" Microstrip	PCB	Taconic TLX-8 RF35, 0.031", $\epsilon_r = 2.55$

**Figure 1. MRF7S18125BHR3(HSR3) Test Circuit Schematic**

**Table 5. MRF7S18125BHR3(HSR3) Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
C1	1 $\mu$ F, 50 V Chip Capacitor	12065G105AT2A	AVX
C2, C3, C4, C5	4.7 $\mu$ F, 50 V Chip Capacitors	GRM55ER71H475KA01L	Murata
C6	220 $\mu$ F, 63 V Electrolytic Chip Capacitor	2222 136 68221	Vishay
C7, C8, C9, C10, C11	6.8 pF Chip Capacitors	ATC100B6R8BT500XT	ATC
C12, C13	1 pF Chip Capacitors	ATC100B1R0BT500XT	ATC
C14, C15, C16, C17, C18	0.2 pF Chip Capacitors	ATC100B0R2BT500XT	ATC
R1, R2	10 k $\Omega$ , 1/4 W Chip Resistors	CRCW12061001FKEA	Vishay
R3	10 $\Omega$ , 1/4 W Chip Resistor	CRCW120610R1FKEA	Vishay

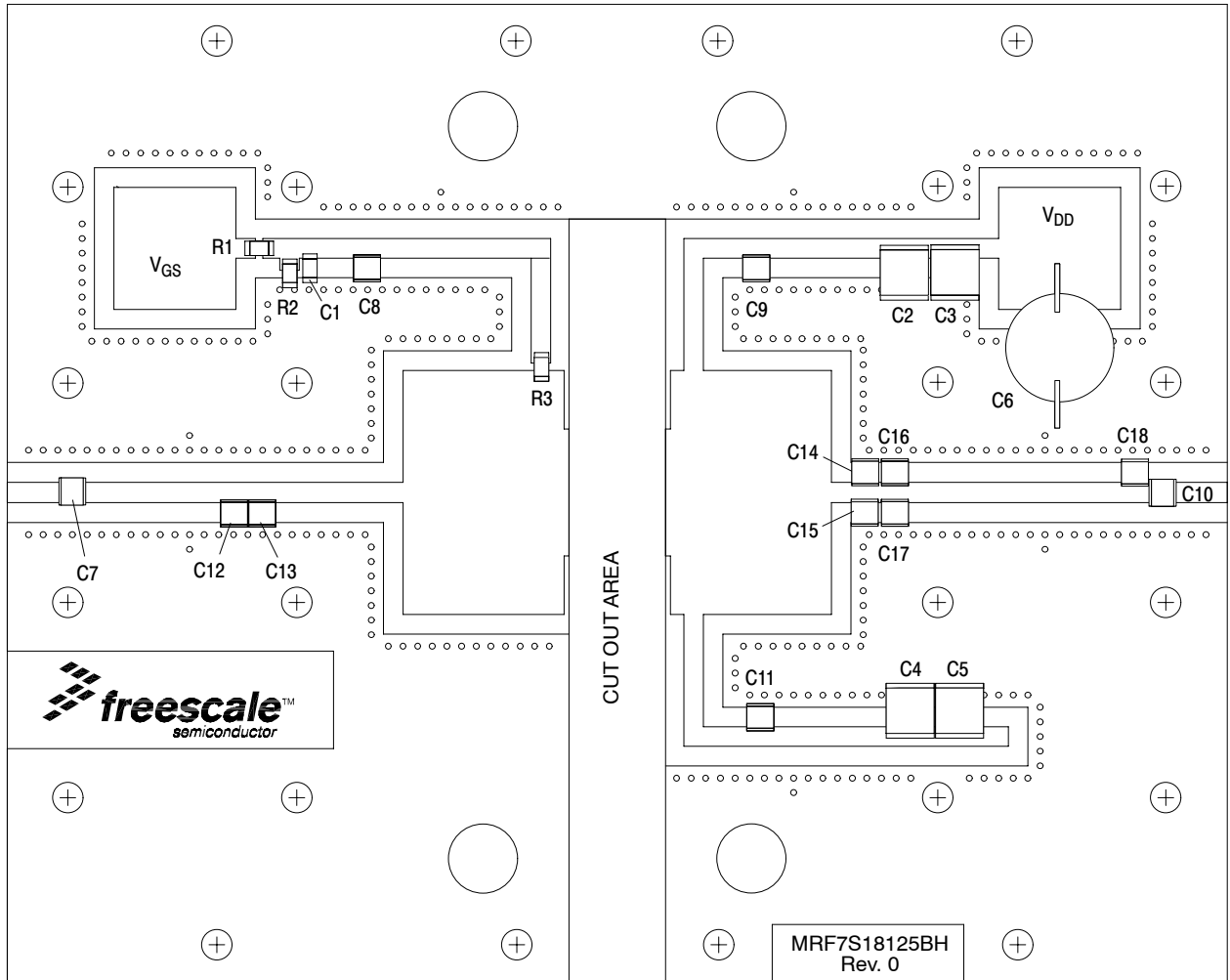


Figure 2. MRF7S18125BHR3(HSR3) Test Circuit Component Layout

### TYPICAL CHARACTERISTICS

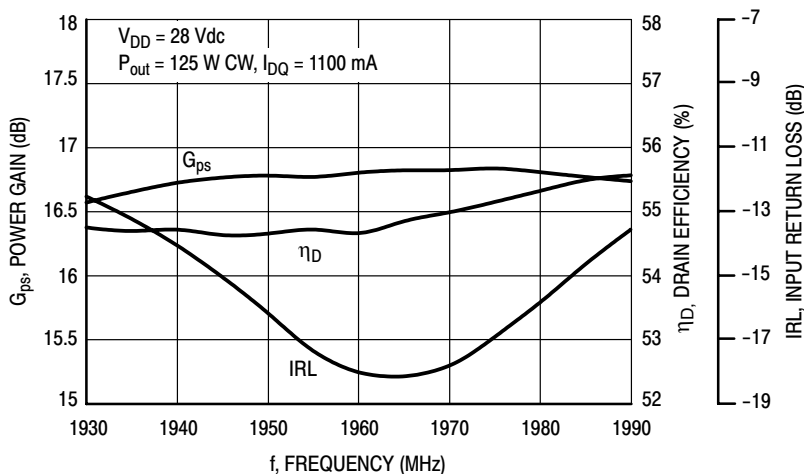


Figure 3. Power Gain, Input Return Loss and Drain Efficiency versus Frequency @  $P_{out} = 125$  Watts CW

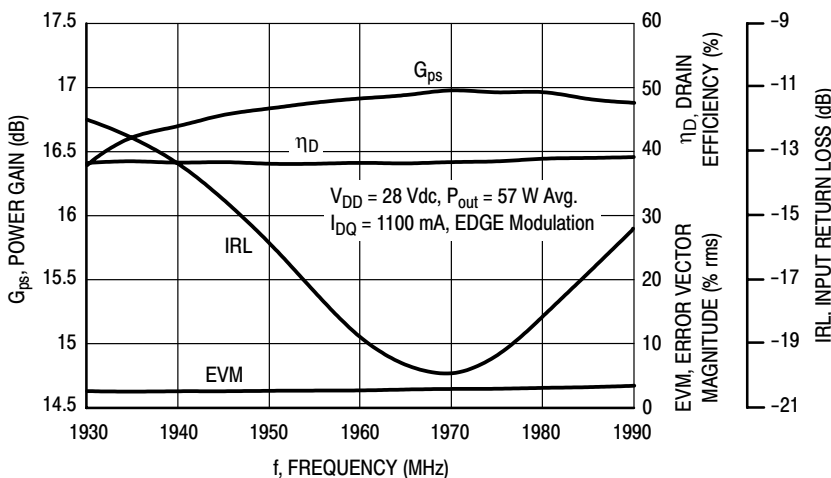


Figure 4. Power Gain, Input Return Loss, EVM and Drain Efficiency versus Frequency @  $P_{out} = 57$  Watts Avg.

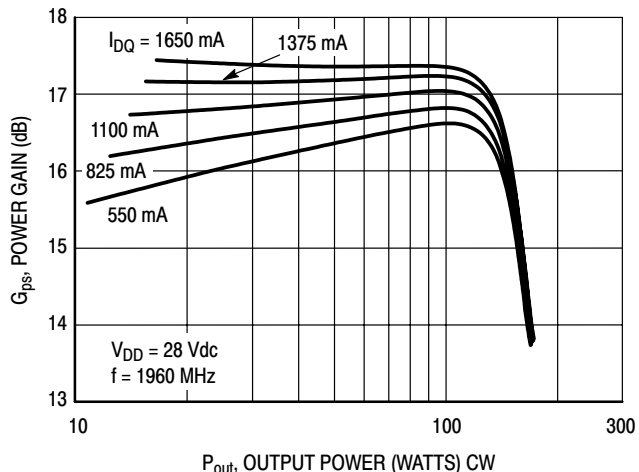


Figure 5. Power Gain versus Output Power

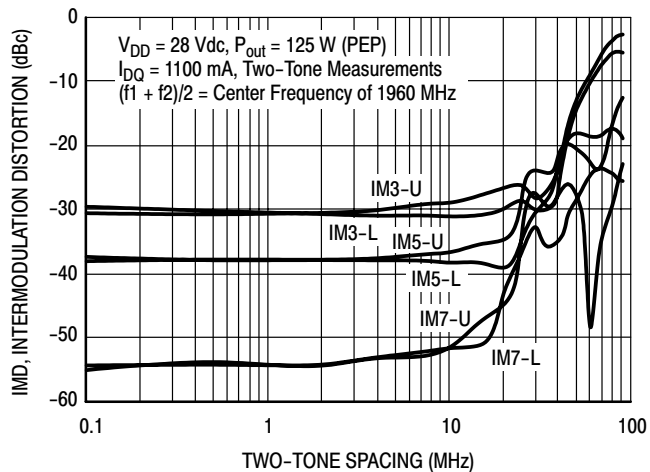
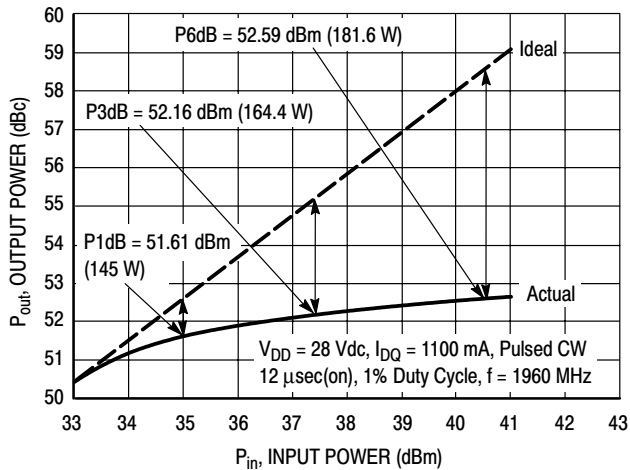
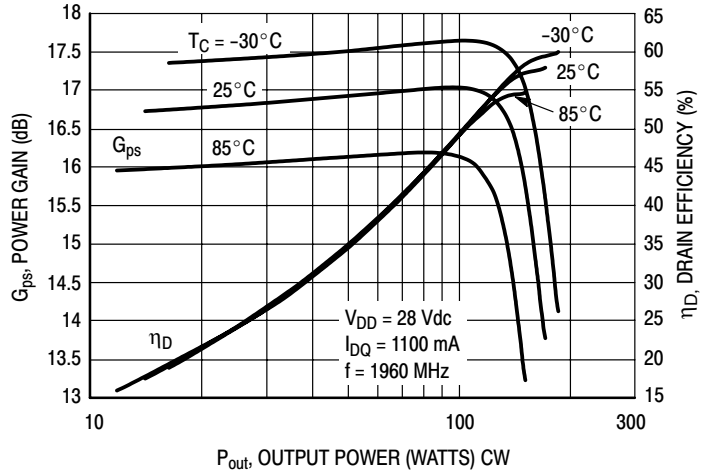


Figure 6. Intermodulation Distortion Products versus Two-Tone Spacing

## TYPICAL CHARACTERISTICS



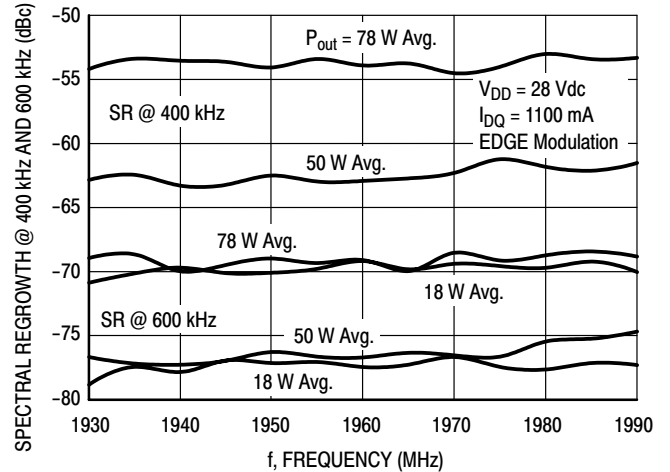
**Figure 7. Pulsed CW Output Power versus Input Power**



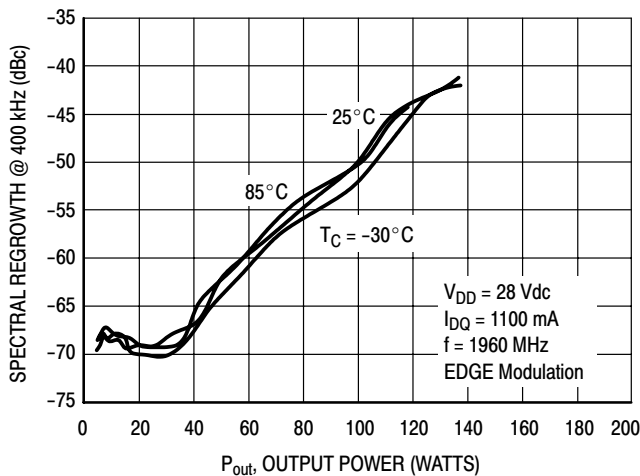
**Figure 8. Power Gain and Drain Efficiency versus Output Power**



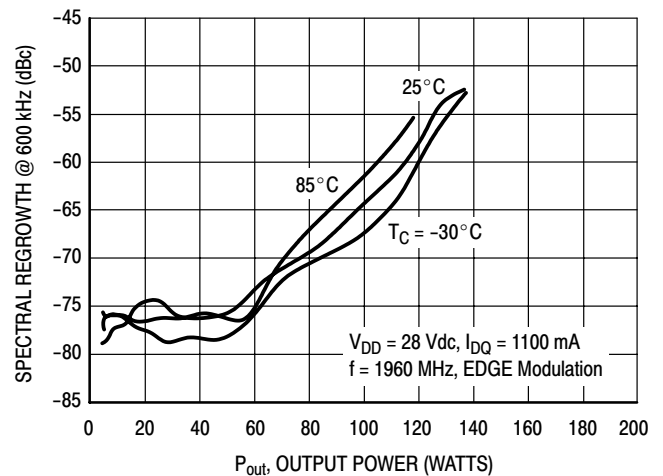
**Figure 9. EVM versus Frequency**



**Figure 10. Spectral Regrowth at 400 kHz and 600 kHz versus Frequency**

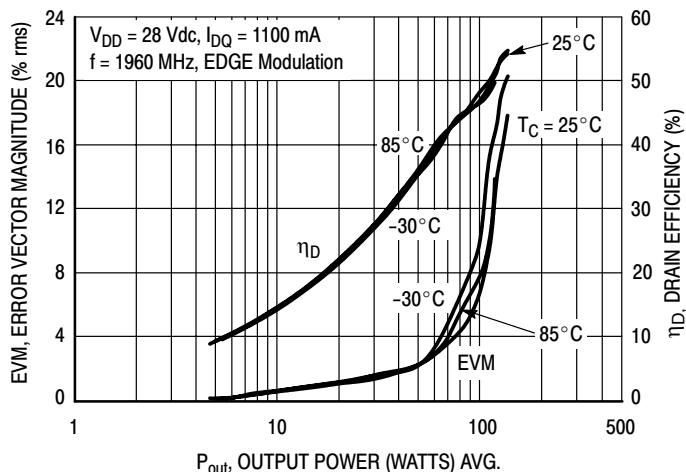


**Figure 11. Spectral Regrowth at 400 kHz versus Output Power**

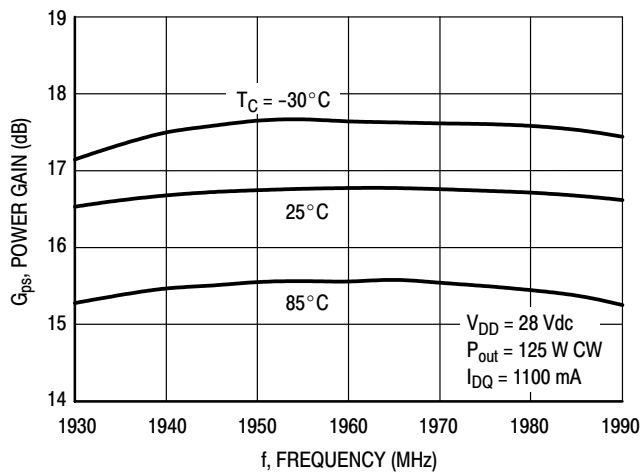


**Figure 12. Spectral Regrowth at 600 kHz versus Output Power**

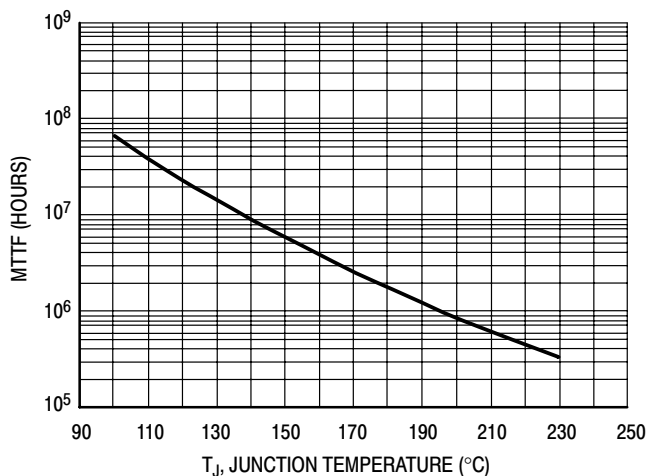
## TYPICAL CHARACTERISTICS



**Figure 13. EVM and Drain Efficiency versus Output Power**



**Figure 14. Power Gain versus Frequency**



This above graph displays calculated MTTF in hours when the device is operated at  $V_{DD} = 28$  Vdc,  $P_{out} = 125$  W CW, and  $\eta_D = 55\%$ .

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

**Figure 15. MTTF versus Junction Temperature**



## GSM TEST SIGNAL

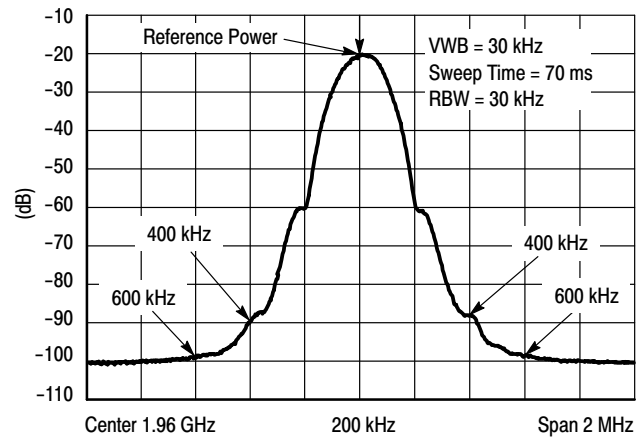
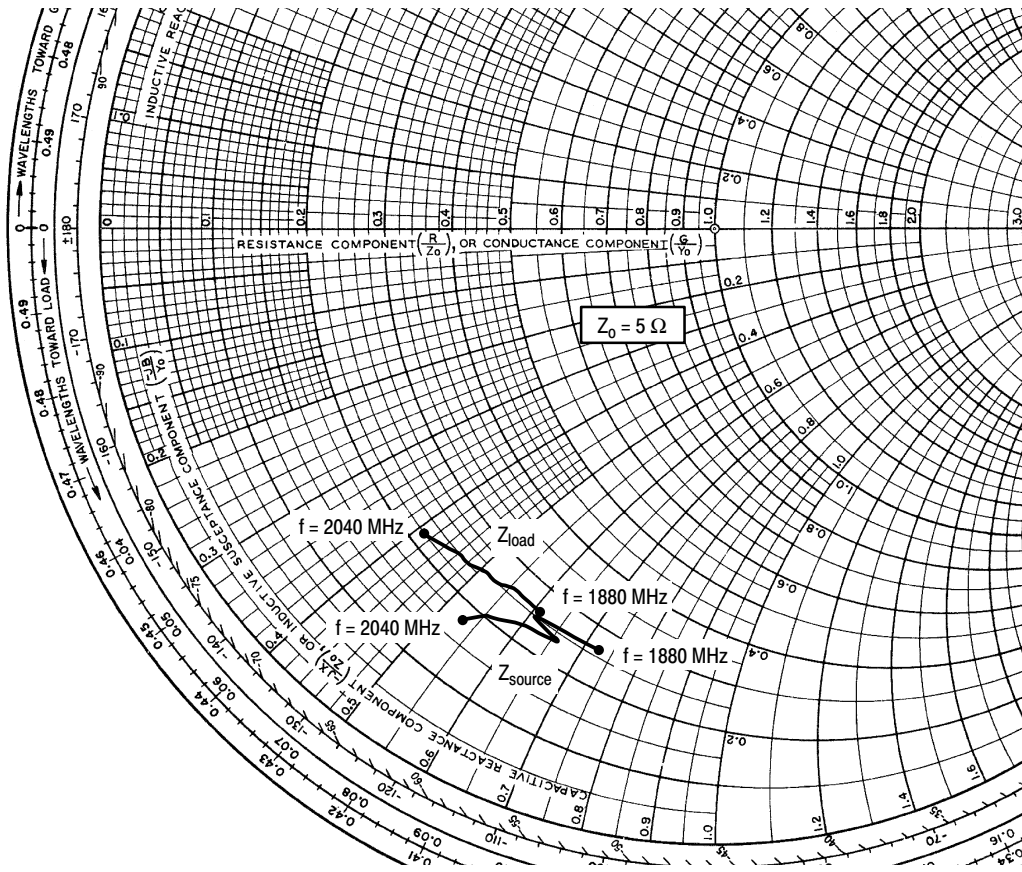


Figure 16. EDGE Spectrum



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 1100 \text{ mA}$ ,  $P_{out} = 125 \text{ W CW}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
1880	$1.31 - j3.61$	$1.32 - j3.06$
1900	$1.25 - j3.06$	$1.30 - j2.92$
1920	$1.21 - j3.30$	$1.28 - j2.79$
1940	$1.17 - j3.17$	$1.26 - j2.67$
1960	$1.13 - j3.06$	$1.23 - j2.55$
1980	$1.10 - j2.92$	$1.20 - j2.42$
2000	$1.06 - j2.83$	$1.18 - j2.30$
2020	$0.99 - j2.75$	$1.16 - j2.18$
2040	$0.91 - j2.66$	$1.12 - j2.07$

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

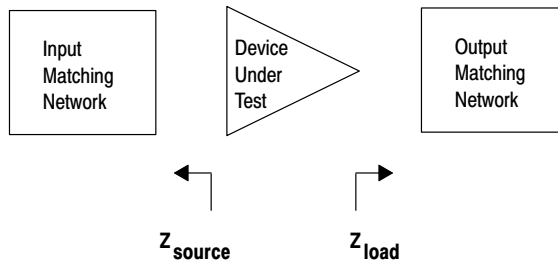
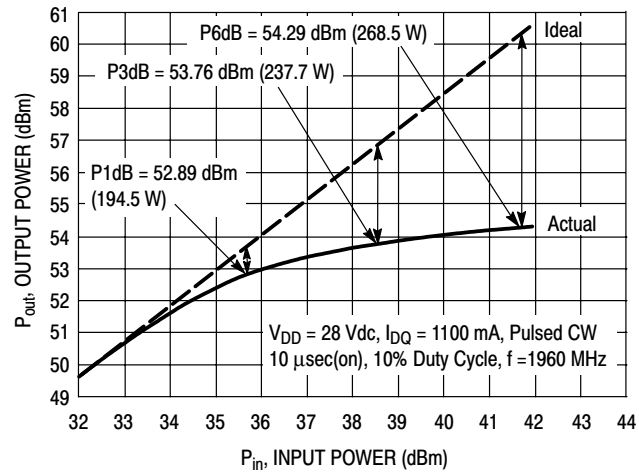


Figure 17. Series Equivalent Source and Load Impedance

## ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS



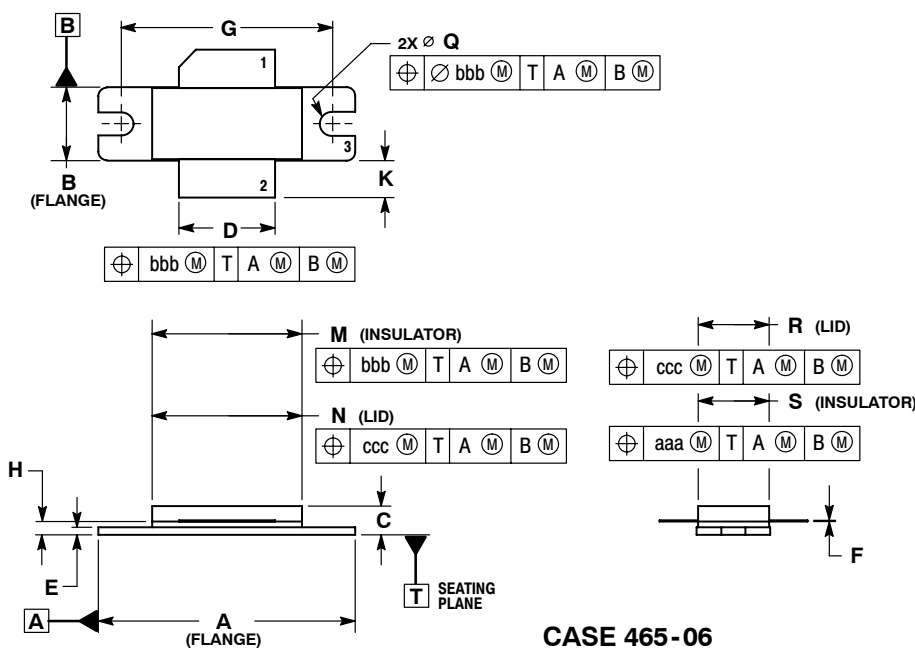
NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

Test Impedances per Compression Level

	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
P1dB	0.65 - j4.06	0.73 - j2.62

Figure 18. Pulsed CW Output Power versus Input Power @ 28 V

## PACKAGE DIMENSIONS

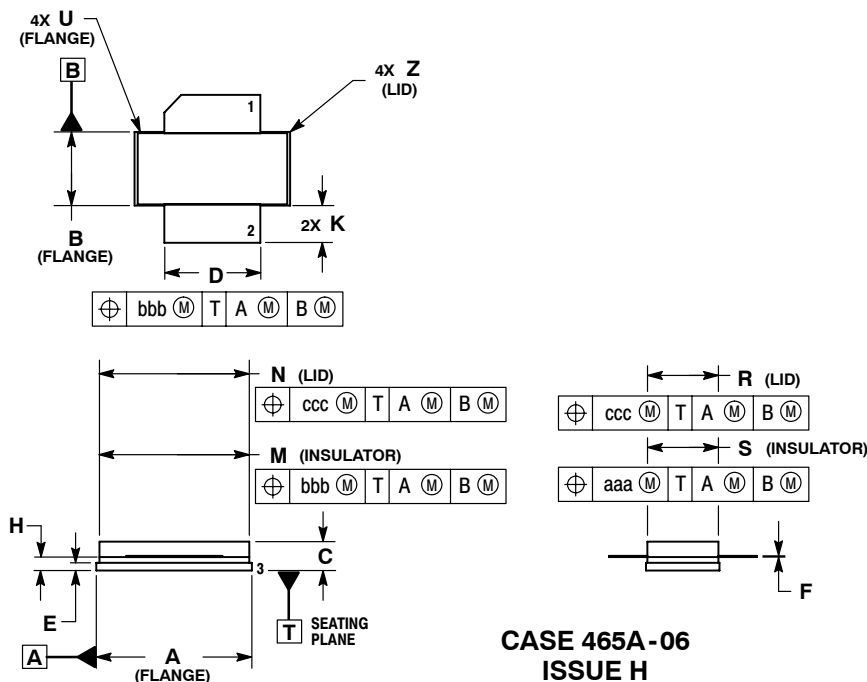


**CASE 465-06  
ISSUE G  
NI-780  
MRF7S18125BHR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DELETED
  4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	∅.118	∅.138	∅3.00	∅3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE



**CASE 465A-06  
ISSUE H  
NI-780S  
MRF7S18125BHSR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DELETED
  4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
5. SOURCE

## PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

### Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Nov. 2008	<ul style="list-style-type: none"><li>• Initial Release of Data Sheet</li></ul>

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### **Japan:**

Freescale Semiconductor Japan Ltd.  
Headquarters  
ARCO Tower 15F  
1-8-1, Shimo-Meguro, Meguro-ku,  
Tokyo 153-0064  
Japan  
0120 191014 or +81 3 5437 9125  
[support.japan@freescale.com](mailto:support.japan@freescale.com)

### **Asia/Pacific:**

Freescale Semiconductor China Ltd.  
Exchange Building 23F  
No. 118 Jianguo Road  
Chaoyang District  
Beijing 100022  
China  
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